

# 10MHz, RRIO, CMOS Operational Amplifier for Cost-Sensitive Systems

## **General Description**

ETQ85604 is a quad low-voltage (1.8 V to 5.5 V) operational amplifier (op amp) with rail-to-rail input- and output- swing capabilities. The device is highly cost-effective solutions for applications where low-voltage operation, a small footprint, and high capacitive load drive are required. Although the capacitive load drive of the ETQ85604 is 100 pF, the resistive open-loop output impedance makes stabilizing with higher capacitive loads simpler.

ETQ85604 is specified for the extended industrial/automotive temperature range (-40°C to +125°C). It is available in SOP14 package.

#### **Features**

- Rail-to-rail input and output
- Low input offset voltage: ±0.3 mV
- Unity-gain bandwidth: 10 MHz
- Low broadband noise: 10 nV/√Hz
- Low input bias current: ±5 pA
- Low quiescent current: 550 μA
- Unity-gain stable
- Internal RFI and EMI filter
- Operational supply voltage range 1.8 V to 5.5V
- Easier to stabilize with higher capacitive load due to resistive open-loop output impedance

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- Automotive AEC-Q100 Grade 1 Qualified
  - -- Extended temperature range of -40°C to +125°C
  - -- ESD HBM 2.5KV PASS
  - -- ESD CDM 1KV PASS

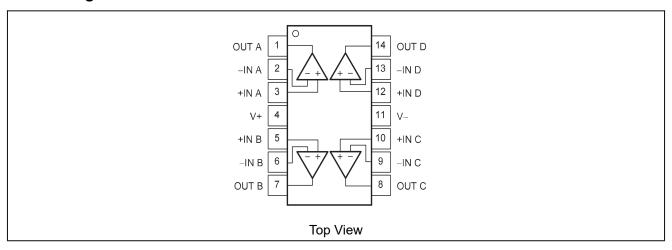
#### **Applications**

- Temperature sensors
- Smoke detectors
- Wearable devices
- Laptop computers
- Sensor signal conditioning
- Power modules
- Active filters
- Low-side current sensing

#### **Device information**

Part No.	Package	MSL	
ETQ85604M	SOP14	1	

## **Pin Configuration**



#### **Pin Function**

Pin Number	Symbol	Descriptions	
1,7,8,14	OUT	Output	
11	V-	Negative supply	
3,5,10,12	+IN	Non-inverting input	
2,6,9,13	-IN	Inverting input	
4	V+	Positive supply	

#### **Functional Description**

#### **Operating Voltage**

ETQ85604 operates from 1.8 V to 5.5 V, is unity-gain stable, and is designed for a wide range of general-purpose applications.

#### Rail-to-Rail Input

The input common-mode voltage range extends 100 mV beyond the supply rails for the full supply voltage range of 1.8 V to 5.5 V. This performance is achieved with a complementary input stage.

#### Rail-to-Rail Output

Designed as a low-power, low-voltage operational amplifier, the ETQ85604 delivers a robust output drive capability. A class AB output stage with common-source transistors achieves full rail-to-rail output swing capability. For resistive loads of 10 k $\Omega$ , the output swings to within 15 mV of either supply rail, regardless of the applied power-supply voltage. Different load conditions change the ability of the amplifier to swing close to the rails.

## **Absolute Maximum Ratings**

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are only stress ratings, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions are not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

Symbol Parameter		Value	Unit
Vs	Supply Voltage:(V+) - (V-)	0 to 6	V
V <sub>IC</sub>	Common-mode Input Voltage <sup>(1)</sup>	(V-)-0.5 to (V+)+0.5	V
V <sub>ID</sub>	Differential Input Voltage <sup>(1)</sup>	(V+) - (V-)+0.2	V
I <sub>IN</sub>	Signal input terminals Current <sup>(1)</sup>	s Current <sup>(1)</sup> -10 to +10	
Isc	Output short-circuit current <sup>(2)</sup>	Continuous	
\/	ESD (Human Body Model) <sup>(3)</sup>	±2500	V
V <sub>ESD</sub>	ESD (Component Discharge Model) <sup>(4)</sup>	±1000	V
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C
T <sub>J(MAX)</sub>	Max Junction Temperature Range	+150	°C

**Note1**: Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5 V beyond the supply rails should be current limited to 10 mA or less.

Note2: Short-circuit to ground, one amplifier per package.

Note3: HBM tested per AEC-Q100-002(EIA/JESD22-A114);

Note4: CDM tested per AEC-Q100-011(EIA/JESD22-C101);

#### **Thermal Characteristics**

Symbol	Package	Ratings	Value	Unit
$R_{ heta JA}$	SOP14	Thermal Characteristics,	107	°C/W
	30714	Thermal Resistance, Junction-to-Air	107	C/VV

## **Recommended Operating Conditions**

Symbol	Symbol Parameter		Unit
Vs	Supply Voltage: (V+) - (V-)	1.8(±0.9) ~ 5.5(±2.75)	V
T <sub>A</sub>	Operating Temperature Range	-40 ~ +125	°C

## **Electrical Characteristics**

 $V_S$  = (V+) – (V-) = 1.8 V to 5.5 V (±0.9 V to ±2.75 V),  $T_A$  = 25°C,  $R_L$  = 10 k $\Omega$  connected to  $V_S/2$ , and  $V_{CM}$  =  $V_{OUT}$  =  $V_S/2$  (unless otherwise noted)

Symbol	Parameter	Conditions Min		Тур	Max	Unit
OFFSET	VOLTAGE				•	
Vos	loon of affect valtage	V <sub>S</sub> = 5 V		±0.3	±2.5	
	Input offset voltage	V <sub>S</sub> = 5 V, T <sub>A</sub> = -40°C to 125°C			±3.5	mV
ΔV <sub>OS</sub> /ΔT	Input offset voltage	V <sub>S</sub> = 5 V, T <sub>A</sub> = -40°C to 125°C		±0.53		11/1/°C
Δνος /Δι	vs temperature	Vs - 5 V, TA40 C to 125 C		±0.55		μV/°C
PSRR	Input offset voltage	$V_{\rm S}$ = 1.8 to 5.5 V, $V_{\rm CM}$ = (V-)		±7	±80	μV/V
FOILIT	vs power supply	VS = 1.0 to 3.5 V, VCM = (V-)		±1	100	μν/ν
INPUT V	OLTAGE RANGE					
V <sub>CM</sub>	Common-mode voltage range	V <sub>S</sub> = 1.8 V to 5.5 V	(V-)-0.1		(V+)+0.1	V
		V <sub>S</sub> = 5.5 V,				
		$(V-) - 0.1 V < V_{CM} < (V+) - 1.4 V,$	70	103		
		T <sub>A</sub> = -40°C to 125°C				
		V <sub>S</sub> = 5.5 V,				1
		VCM = -0.1 V to 5.6 V,	57	75		
CMDD	Common-mode rejection ratio	T <sub>A</sub> = -40°C to 125°C				4D
CMRR		V <sub>S</sub> = 1.8 V,				dB
		(V-) - 0.1 V < VCM < (V+) - 1.4 V,		88		
		T <sub>A</sub> = -40°C to 125°C				
		V <sub>S</sub> = 1.8 V,				
		VCM = -0.1 V to 1.9 V,		70		
		$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$				
INPUT B	IAS CURRENT					
lΒ	Input bias current	V <sub>S</sub> = 5 V		±5		pА
los	Input offset current			±5		pА
NOISE						
En	Input voltage noise	f = 0.1 Hz to 10 Hz, V <sub>s</sub> = 5 V		4.77		μV <sub>PP</sub>
⊏n	(peak to peak)	J = 0.1112 to 10112, Vs = 3 V		4.77		μνρρ
0	Input voltage	f = 1 kHz, V <sub>S</sub> = 5 V		16		 −nV/√Hz
e <sub>n</sub>	noise density	$f = 10 \text{ kHz}, V_S = 5 \text{ V}$		10		110/ 1112
i	Input current	f = 1 kHz, V <sub>S</sub> = 5 V		23		fA/√Hz
i <sub>n</sub>	noise density <sup>(5)</sup>	) - 1 KHZ, VS - 3 V	23			I/A/ VI IZ
INPUT C	APACITANCE					
$C_{ID}$	Differential <sup>(5)</sup>			2		pF
$C_{IC}$	Common-mode <sup>(5)</sup>			4		pF

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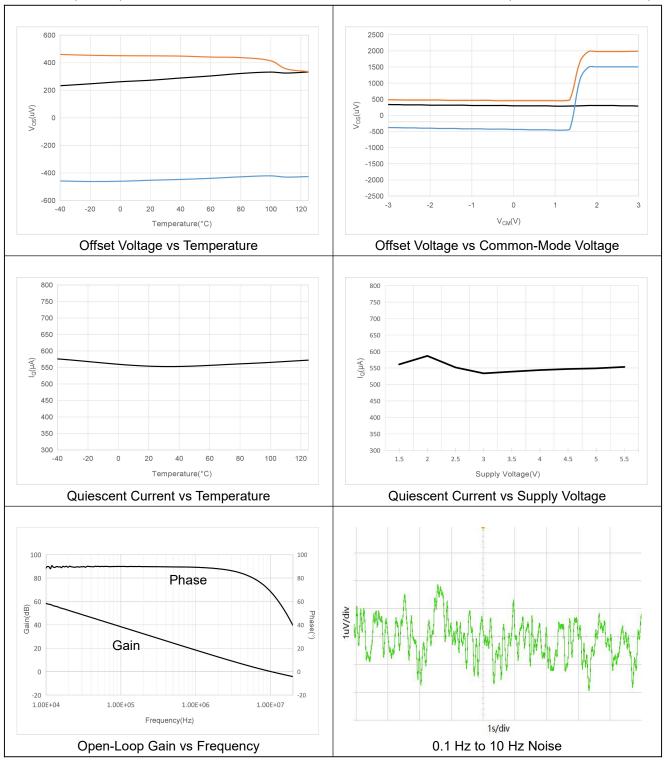
# **Electrical Characteristics (Continued)**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
OPEN-LO	OOP GAIN					
		$V_{S} = 1.8 \text{ V}, R_{L} = 10 \text{ k}\Omega$		100		٩D
		$(V-) + 0.04 V < V_O < (V+) - 0.04 V$		100		dB
		$V_{S} = 5.5 \text{ V}, R_{L} = 10 \text{ k}\Omega$	104	120		
۸	Open-loop	$(V-) + 0.1 V < V_0 < (V+) - 0.1 V$	104	130		
$A_{OL}$	voltage gain	$V_S = 1.8 \text{ V}, R_L = 2 \text{ k}\Omega$		100		
		$(V-) + 0.06 V < V_0 < (V+) - 0.06 V$		100		
		$V_S = 5.5 \text{ V}, R_L = 2 \text{ k}\Omega$		130		dB
		$(V-) + 0.15 V < V_0 < (V+) - 0.15 V$		130		uБ
FREQUE	NCY RESPONSE					
GBW	Gain-bandwidth product	V <sub>S</sub> = 5 V, G =+1		10		MHz
φm	Phase margin	V <sub>S</sub> = 5 V, G =+1		55		0
SR	Slew rate	V <sub>S</sub> = 5 V, G =+1		6		V/µs
		To 0.1%, V <sub>S</sub> = 5 V, 2V step,		0.5		
<b>4</b> -	Sottling time(5)	$G = +1, C_L = 100 pF$		0.5		μs
<b>t</b> s	Settling time <sup>(5)</sup>	To 0.01%, V <sub>S</sub> = 5 V, 2V step,		1		
		G = +1, C <sub>L</sub> = 100 pF		Į.		
t <sub>OR</sub>	Overload recovery time	V <sub>S</sub> = 5 V, V <sub>IN</sub> × gain > V <sub>S</sub>		0.2		μs
TUDAN	Total harmonic	$V_S = 5.5 \text{ V}, V_{CM} = 2.5 \text{ V},$		0.0000		0/
THD+N	distortion + noise	$V_0 = 1 V_{RMS}, G = +1, f = 1 kHz$		0.0008		%
OUTPUT	•					
V-	Voltage output swing	$V_{S} = 5.5 \text{ V}, R_{L} = 10 \text{ k}\Omega$			20	m\/
Vo	from supply rails	$V_S = 5.5 \text{ V}, R_L = 2 \text{ k}\Omega$			60	mV
Isc	Short-circuit current	V <sub>S</sub> = 5 V		±50		mA
Zo	Open-loop output impedance <sup>(5)</sup>	V <sub>S</sub> = 5 V, <i>f</i> = 10MHz		100		Ω
POWER	SUPPLY					
Vs	Specified voltage range		1.8 (±0.9)		5.5 (±2.75)	V
		$I_0 = 0 \text{ mA}, V_S = 5.5 \text{ V}$		550	800	
IQ	Quiescent current	$I_0 = 0 \text{ mA}, V_S = 5.5 \text{ V},$				μA
~	per amplifier	$T_A = -40^{\circ}C \text{ to } 125^{\circ}C$			850	•

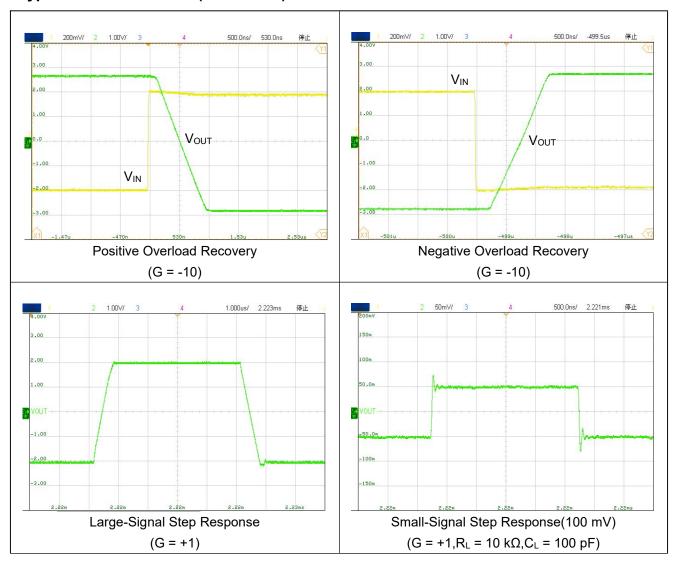
Note5: Guaranteed by design.

## **Typical Characteristics**

 $V_S = 5.5 \text{ V}(\pm 2.75 \text{V}), V_{CM} = V_{OUT} = V_S/2, \text{ and } R_L = 10 \text{k}\Omega \text{ connected to } V_S/2, T_A = 25 ^{\circ}\text{C} \text{ (unless otherwise noted)}$ 



# **Typical Characteristics (Continued)**



#### **Layout Guidelines**

For best operational performance of the device, use good PCB layout practices, including:

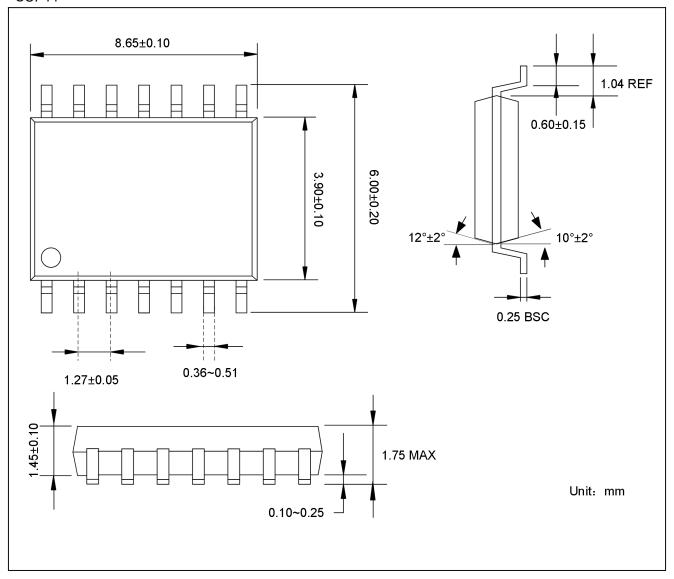
Place the external components as close to the device as possible. This configuration prevents parasitic errors (such as the Seebeck effect) from occurring.

To reduce parasitic coupling, run the input traces as far away from the supply lines and digital signal as possible.Low-ESR,  $0.1~\mu F$  ceramic bypass capacitors must be connected between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable to single supply applications.

Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

# **Package Dimension**

## SOP14



# **Revision History and Checking Table**

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
0.0	2023-04-21	Preliminary Version	Huyt	Wanggp	Liujy
1.0	2023-08-31	Original Version	Huyt	Chenh	Liujy
1.1	2023-9-27	Naming updates	Shibo	Wanggp	Liujy
1.2	2023-10-19	ETQ version	Shibo	Wanggp	Liujy
1.3	2025-3-24	Update Typical Characteristics	Huyt	Tangyx	Liujy